

INTERNATIONAL GEMOLOGICAL INSTITUTE

ELECTRONIC COPY

LABORATORY GROWN DIAMOND REPORT

PROPORTIONS

CLARITY CHARACTERISTICS

KEY TO SYMBOLS

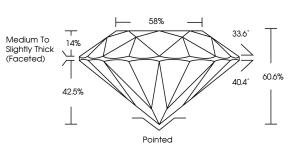
Red symbols indicate internal characteristics.

Green symbols indicate external characteristics.

September 13, 2024	
IGI Report Number	LG652429135
Description	LABORATORY GROWN DIAMOND
Shape and Cutting Style	ROUND BRILLIANT
Measurements	6.40 - 6.45 X 3.90 MM
GRADING RESULTS	
Carat Weight	1.00 CARAT
Color Grade	D
Clarity Grade	VS 1
Cut Grade	IDEAL
ADDITIONAL GRADING I	NFORMATION

Polish	EXCELLENT
Symmetry	EXCELLENT
Fluorescence	NONE
Inscription(s)	低到 LG652429135

Comments: This Laboratory Grown Diamond was created by Chemical Vapor Deposition (CVD) growth process. Type IIa



LG652429135

Report verification at igi.org



Sample Image Used

	September 13, 2024
LG652429135	IGI Report Number
ATORY GROWN DIAMOND	Description LABC
ROUND BRILLIANT	Shape and Cutting Style
6.40 - 6.45 X 3.90 MM	Measurements
	GRADING RESULTS
1.00 CARAT	Carat Weight
D	Color Grade
VS 1	Clarity Grade
IDEAL	Cut Grade

LABORATORY GROWN DIAMOND REPORT

58% 33.6° 149 Medium To Slightly 60.6% Thick 40.4° 42.5% (Faceted) Pointed

ADDITIONAL GRADING INFORMATION

Polish	EXCELLENT
Symmetry	EXCELLENT
Fluorescence	NONE
Inscription(s)	(G) LG652429135
Comments: This Laboratory created by Chemical Vap- process. Type IIa	Grown Diamond was or Deposition (CVD) growth



DEF	GHIJ	Faint	Very Light	Light
CLARITY				
IF	VVS ¹⁻²	VS ¹⁻²	SI ¹⁻²	1-3
Internally Flawless	Very Very Slightly Included	Very Slightly Included	Slightly Included	Included



24 62429135	MM	1.00 CARAT	•	NS I	IDEAL	60.6%	26%	Medium To Slightly Thick (Faceted)	Pointed	EXCELLENT	EXCELLENT	NONE	(g) LG652429135	Comments: The Locatory Grown Damond was acreded by Channed Vapor Deposition (CVD) growth process. Type IId
September 13, 2024 1GI Report No LG662429135 ROUND BRILLIANT	6.40 - 6.45 X 3.90 MM	Carat Weight	Color Grade	Clarity Grade	Out Grade	Depth	Table	Girdle	Culet	Polish	Symmetry	Fluorescence	Inscription(s)	Comments: This Laboratory Grown created by Chemical (CVD) growth process Type lia



	WS ¹⁻²	VS ¹⁻²	SI ¹⁻²	٨Ç
Internally	VVS Very Very	Very	Slightly	In

